Erratum: Study of GaN thin layers subjected to high-temperature rapid thermal annealing [Semiconductors 32, 1048–1053 (October 1998)]

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[S1063-7826(99)02701-5]

On page 1048, the first sentence of Sec. 2 should read “RHTA was performed in a quartz reactor at 1000 °C for 30 s in a stream of N₂ or Ar.”

Translated by M. E. Alferieff